P-Channel 200-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Appl	licatior	IS:
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- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

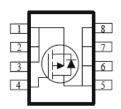
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-200	220 @ V _{GS} = -10V	-4.0		
-200	$235 @ V_{GS} = -5.5V$	-3.9		



FREE







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-200	V	
Gate-Source Voltage			±20	V	
Continuous Dusin Commenta	T _A =25°C		-4.0		
Continuous Drain Current ^a	T _A =70°C	I _D	-3.2	Α	
Pulsed Drain Current ^b			-20		
Continuous Source Current (Diode Conduction) a			-7.1	Α	
Davies Dissinction ^a	T _A =25°C		5	W	
Power Dissipation ^a	T _A =70°C	l P	3.2	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Operating Junction and Storage Temperature Range			-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

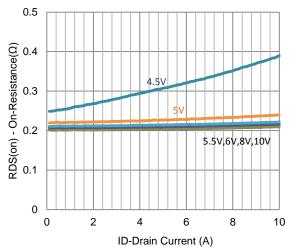
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	$/, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ -25		-25	I UA	
On-State Drain Current	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10			Α	
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_D = -3.2 \text{ A}$			220	mΩ	
Diam-Source On-Resistance	r _{DS(on)}	$V_{GS} = -5.5 \text{ V}, I_D = -2.6 \text{ A}$			235	11122	
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -3.2 \text{ A}$		30		S	
Diode Forward Voltage	V_{SD}	$I_S = -3.6 \text{ A}, V_{GS} = 0 \text{ V}$		-0.78		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = -100 \text{ V}, V_{GS} = -5.5 \text{ V},$		67			
Gate-Source Charge	Q_{gs}	$V_{DS} = -100 \text{ V}, V_{GS} = -3.5 \text{ V},$ $I_{D} = -3.2 \text{ A}$		27		nC	
Gate-Drain Charge	Q_{gd}	1 _D = -3.2 A		28			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -100 \text{ V}, R_L = 31.3 \Omega,$		13			
Rise Time	t _r	$V_{DS} = -100 \text{ V}, R_L - 31.3 \Omega,$ $I_D = -3.2 \text{ A},$		26		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		143		ns	
Fall Time	t _f	V GEN = 10 V, T GEN = 0 12		68			
Input Capacitance	C _{iss}			5465			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	248		pF	
Reverse Transfer Capacitance	C _{rss}			174			

Notes

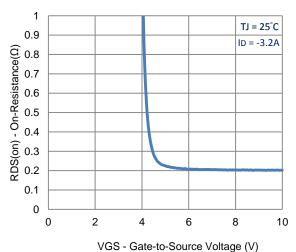
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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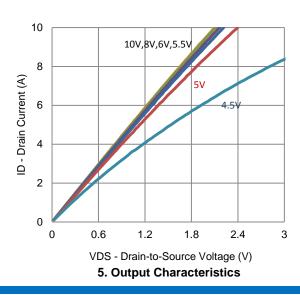
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

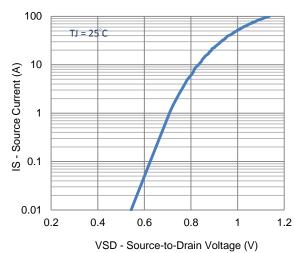


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TJ = 25°C

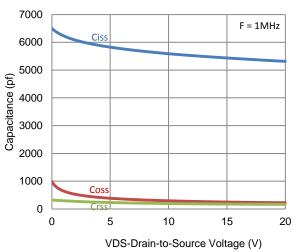
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(Y) tuesun 9
0 0 2 4 6 8

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

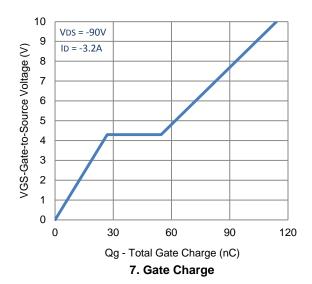


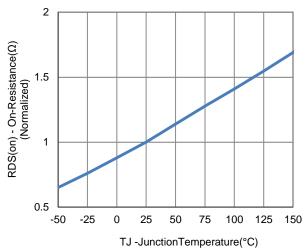
4. Drain-to-Source Forward Voltage

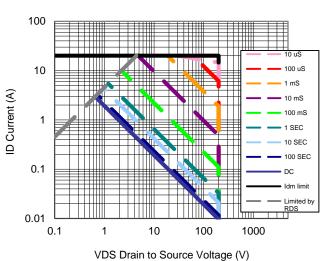


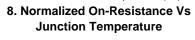
6. Capacitance

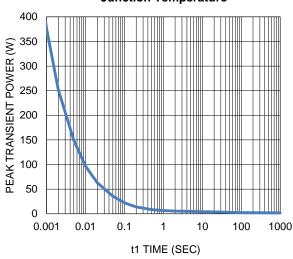
Typical Electrical Characteristics





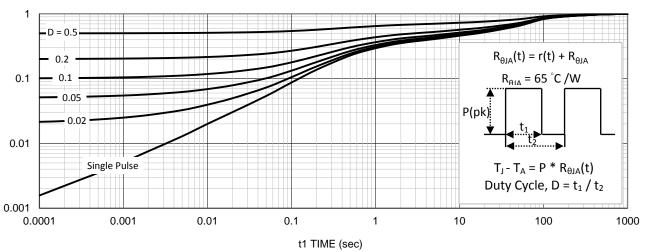






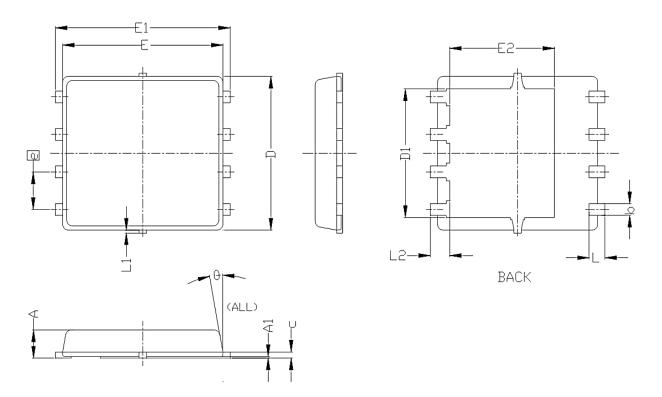
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0. 95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E		5, 55 BSC			0.219 BSC		
El		6.05 BSC		0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2		0.68 REF			0. 027 REF		
θ	0°		10°	0°		10°	